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Vishay Semiconductors

Insulated Gen 2 Schottky Rectifier Module, 250 A



SOT-227

PRIMARY CHARACTERISTICS							
I _{F(AV)} per module at T _C = 106 °C	250 A						
V_{R}	200 V						
V_{FM} at 200 A, $T_C = 25$ °C	1.0 V						
Package	SOT-227						
Circuit configuration	Two separate diodes, parallel pin-out						

FEATURES

- Max. T_{.1} = 175 °C
- Two fully independent diodes
- Fully insulated package
- Trench MOS Barrier Schottky technology
- Ultra low forward voltage drop
- Optimized for power conversion: welding and industrial SMPS applications
- Easy to use and parallel
- · Industry standard outline
- UL approved file E78996
- · Designed and qualified for industrial level
- Material categorization: for definitions of compliance please see <u>www.vishay.com/doc?99912</u>

DESCRIPTION

The VS-QA250FA20 insulated modules integrate two state of the art Trench MOS Schottky technology rectifiers in the compact, industry standard SOT-227 package.

These devices are thus intended for high frequency converters and switching power supplies.

MAJOR RATINGS AND CHARACTERISTICS					
SYMBOL	CHARACTERISTICS	VALUES	UNITS		
V _F	T _J = 125 °C	1.09	V		
T _J	Range	-55 to +175	°C		

ABSOLUTE MAXIMUM RATINGS (T _C = 25 °C unless otherwise specified)					
PARAMETER	SYMBOL	TEST CONDITIONS	VALUES	UNITS	
Maximum average forward current per module	I _{F(AV)}	T _C = 106 °C	250	Α	
Maximum cathode to anode voltage	V _R		200	V	
Maximum continuous forward current per diode	I _F	T _C = 95 °C	183	۸	
Maximum single pulse forward current per diode	I _{FSM}	$T_C = 175$ °C, t = 6 ms, square	900	- A	
Maximum power dissipation per diode	P _D	T _C = 95 °C	182	W	
Non-repetitive avalanche energy per diode	E _{AS}	$T_J = 25 ^{\circ}\text{C}, I_{AS} = 19 \text{A}, L = 10 \text{mH}$	1800	mJ	
RMS isolation voltage	V _{ISOL}	Any terminal to case, t = 1 minute	2500	V	
Operating junction and storage temperatures	T _J , T _{Stg}		-55 to +175	°C	



ELECTRICAL SPECIFICATIONS PER DIODE (T _J = 25 °C unless otherwise specified)						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Cathode to anode breakdown voltage	V_{BR}	I _R = 2 mA	200	-	-	
Formulation of the second state of the second	I _F = 200 A	-	1.0	1.2	V	
Forward voltage	V_{FM}	I _F = 200 A, T _J = 125 °C	-	0.89	1.09	
Reverse leakage current I _{RM}	V _R = 200 V	-	13	90	μΑ	
	T _J = 125 °C, V _R = V _R rated	-	14	-	mA	
Junction capacitance	C _T	V _R = 200 V	-	380	-	pF

DYNAMIC RECOVERY CHARACTERISTICS (T _J = 25 °C unless otherwise specified)							
PARAMETER	SYMBOL	TEST CONDITIONS		MIN.	TYP.	MAX.	UNITS
Reverse recovery time	+	T _J = 25 °C	$I_F = 50 \text{ A}$ $dI_F/dt = 200 \text{ A/}\mu\text{s}$ $V_R = 100 \text{ V}$	-	54	-	ns
neverse recovery time	t _{rr}	T _J = 125 °C		-	67	-	
Dook recovery current	I _{RRM}	T _J = 25 °C		-	6	-	А
Peak recovery current		T _J = 125 °C		-	8.4	-	
Reverse recovery charge Q _{rr}	0	T _J = 25 °C		-	165	-	nC
	T _J = 125 °C		-	296	-	l lic	

THERMAL - MECHANICAL SPECIFICATIONS						
PARAMETER	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNITS
Junction to case, single leg conducting	D		-	-	0.44	
Junction to case, both leg conducting	R_{thJC}		-	-	0.22	°C/W
Case to heatsink	R _{thCS}	Flat, greased surface	-	0.1	-	
Weight			-	30	-	g
Mounting torque		Torque to terminal	-	-	1.1 (9.7)	Nm (lbf.in)
Mounting torque		Torque to heatsink	-	-	1.8 (15.9)	Nm (lbf.in)
Case style				SC	T-227	



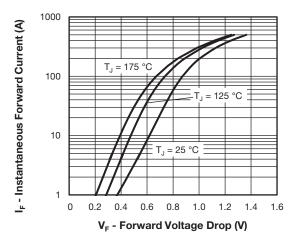


Fig. 1 - Typical Forward Voltage Drop vs. Instantaneous Forward Current (Per Diode)

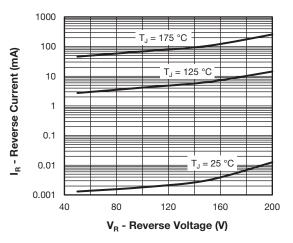


Fig. 2 - Typical Reverse Current vs. Reverse Voltage (Per Diode)

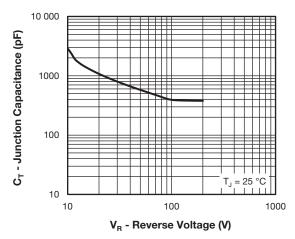


Fig. 3 - Typical Junction Capacitance vs. Reverse Voltage (Per Diode)

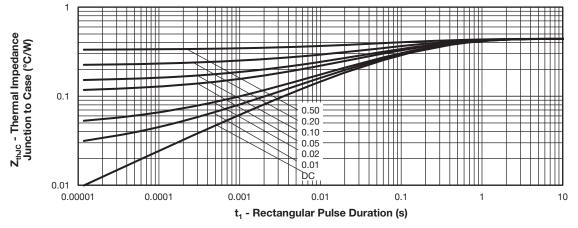


Fig. 4 - Maximum Thermal Impedance Z_{thJC} Characteristics (Per Diode)



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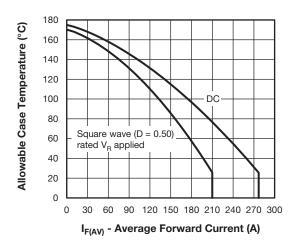


Fig. 5 - Maximum Current Rating Capability (Per Diode)

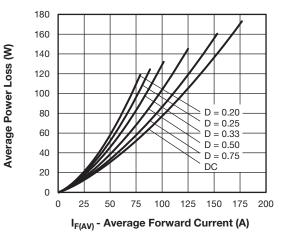


Fig. 6 - Forward Power Loss Characteristics (Per Diode)

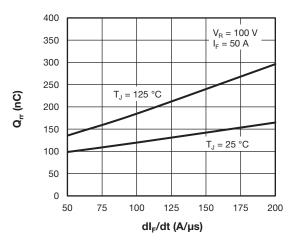


Fig. 7 - Typical Reverse Recovery Charge vs. dl_F/dt (Per Diode)

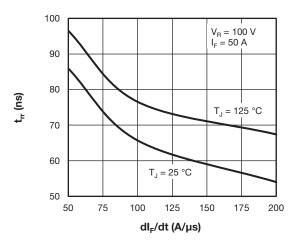


Fig. 8 - Typical Reverse Recovery Time vs. dl_F/dt (Per Diode)

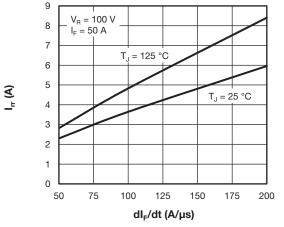


Fig. 9 - Typical Reverse Recovery Current vs. dI_F/dt (Per Diode)



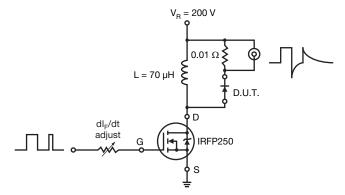
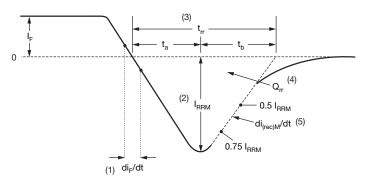


Fig. 10 - Reverse Recovery Parameter Test Circuit



- (1) di_F/dt rate of change of current through zero crossing
- (2) I_{RRM} peak reverse recovery current
- (3) t_{rr} reverse recovery time measured from zero crossing point of negative going I_F to point where a line passing through 0.75 I_{RRM} and 0.50 I_{RRM} extrapolated to zero current.
- (4) \mathbf{Q}_{rr} area under curve defined by \mathbf{t}_{rr} and \mathbf{I}_{RRM}

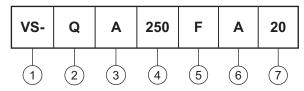
$$Q_{rr} = \frac{t_{rr} \times I_{RRM}}{2}$$

(5) $di_{(rec)M}/dt$ - peak rate of change of current during t_b portion of t_{rr}

Fig. 11 - Reverse Recovery Waveform and Definitions

ORDERING INFORMATION TABLE

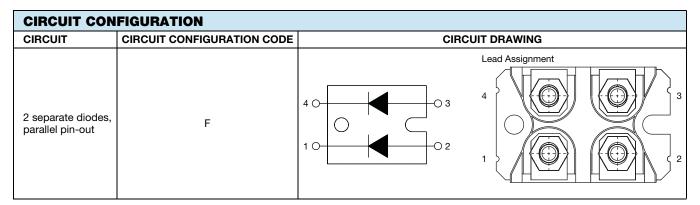
Device code



- 1 Vishay Semiconductors product
- 2 Schottky technologies
- Present silicon generation
- 4 Current rating (250 = 250 A)
- 5 Circuit configuration (2 separate diodes, parallel pin-out)
- 6 Package indicator (SOT-227 standard insulated base)
- 7 Voltage rating (20 = 200 V)

Quantity per tube is 10, M4 screw and washer included

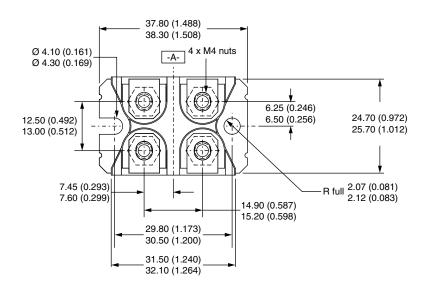


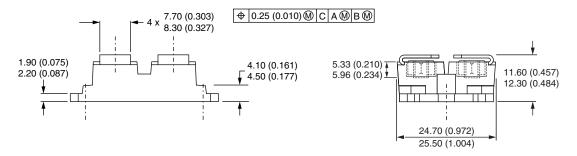


LINKS TO RELATED DOCUMENTS					
Dimensions	www.vishay.com/doc?95423				
Packaging information	www.vishay.com/doc?95425				

SOT-227 Generation 2

DIMENSIONS in millimeters (inches)





Note

· Controlling dimension: millimeter



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